

**ABSTRACT OF THE DISCLOSURE**

A structure for a bond pad used on a semiconductor device, in accordance with the present invention, includes a metal layer, an interconnect formed through a dielectric layer connecting to the metal layer and a bond pad having a first portion disposed over the metal layer and the interconnect, and a second portion disposed over the dielectric layer. The first portion includes a bond area for providing an attachment point for a connection, and the second portion includes a probe area for providing contact with a probe.

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